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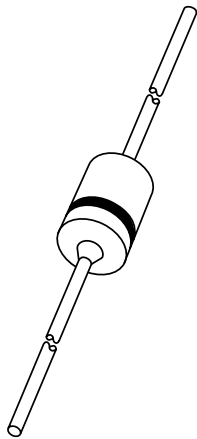
NXP Semiconductors/Freescale Semiconductor, Inc.
1N914B,113

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sales@integrated-circuit.com

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DISCRETE SEMICONDUCTORS

DATA SHEET

1N914; 1N914A; 1N914B
High-speed diodes

Product specification

Supersedes data of 1999 May 26

2003 Jun 06

PHILIPS

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Philips Semiconductors   **Product specification**

High-speed diodes   **1N914; 1N914A; 1N914B**
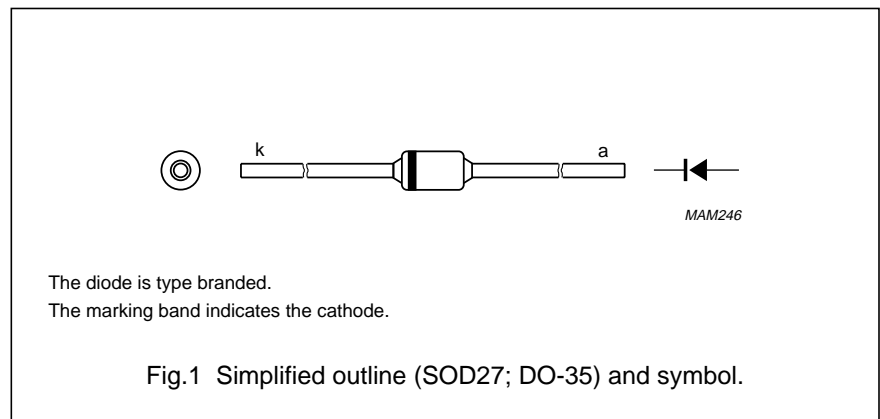
FEATURES

- Hermetically sealed leaded glass SOD27 (DO-35) package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 225 mA.

APPLICATIONS

- High-speed switching.

DESCRIPTION

The 1N914, 1N914A and 1N914B are high-speed switching diodes fabricated in planar technology, and encapsulated in a hermetically sealed leaded glass SOD27 (DO-35) package.

k   a

MAM246

The diode is type branded.
The marking band indicates the cathode.

Fig.1 Simplified outline (SOD27; DO-35) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	100	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	see Fig.2; note 1	–	75	mA
I_{FRM}	repetitive peak forward current		–	225	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\ °C$ prior to surge; see Fig.4			
		t = 1 µs	–	4	A
		t = 1 ms	–	1	A
		t = 1 s	–	0.5	A
P_{tot}	total power dissipation	$T_{amb} = 25\ °C$; note 1	–	250	mW
T_{stg}	storage temperature		−65	+200	°C
T_j	junction temperature		–	175	°C

Note

1. Device mounted on an FR4 printed-circuit board; lead length 10 mm.

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High-speed diodes

1N914; 1N914A; 1N914B

ELECTRICAL CHARACTERISTICS

T_j = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_F	forward voltage	see Fig.3			
	1N914; 1N914A	I_F = 10 mA	–	1	V
	1N914B	I_F = 5 mA	0.62	0.72	V
	1N914B	I_F = 100 mA	–	1	V
I_R	reverse current	see Fig.5			
		V_R = 20 V	–	25	nA
		V_R = 75 V	–	5	μA
		V_R = 20 V; T_j = 150 °C	–	50	μA
C_d	diode capacitance	f = 1 MHz; V_R = 0; see Fig.6	–	4	pF
t_{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	–	8	ns
		when switched from I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	–	4	ns
V_{fr}	forward recovery voltage	when switched from I_F = 50 mA; t_r = 20 ns; see Fig.8	–	2.5	V

THERMAL CHARACTERISTICS

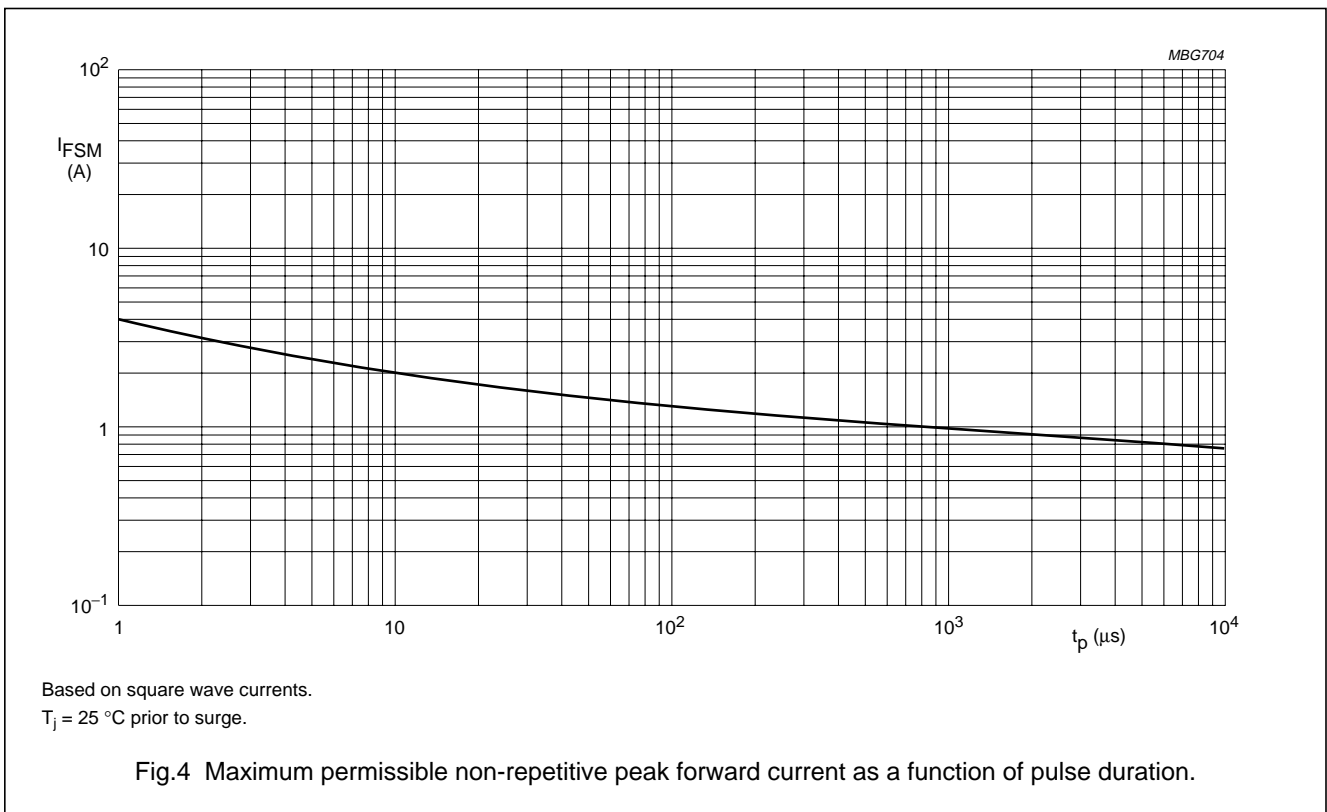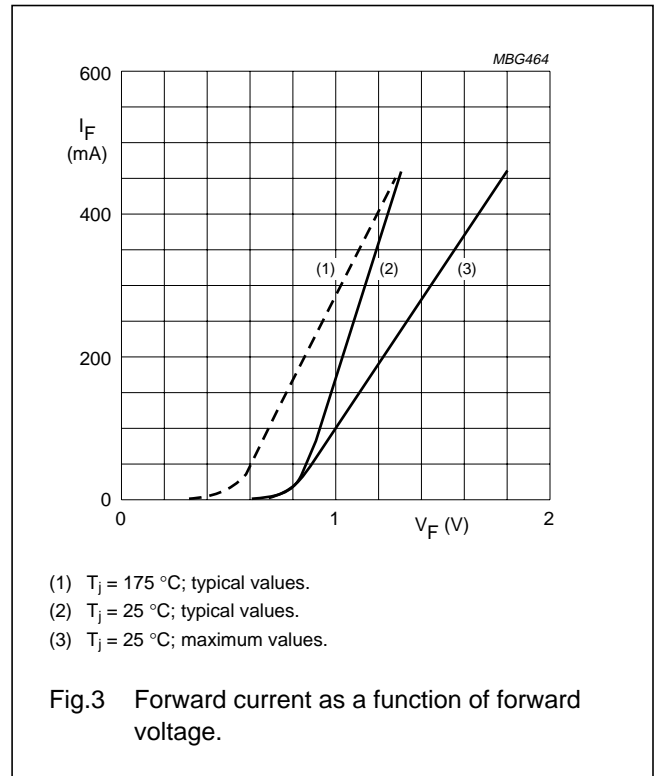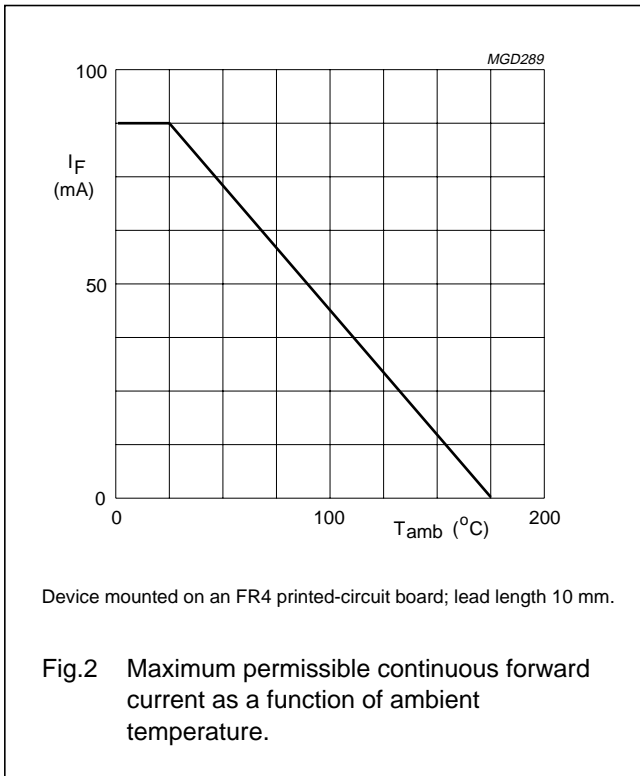| SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point	lead length 10 mm	240	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	lead length 10 mm; note 1	500	K/W

Note

1. Device mounted on a printed-circuit board without metallization pad.

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Product specification

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1N914; 1N914A; 1N914B

GRAPHICAL DATA

Device mounted on an FR4 printed-circuit board; lead length 10 mm.

Fig.2   Maximum permissible continuous forward
current as a function of ambient
temperature.

(1) T_j = 175 °C; typical values.
(2) T_j = 25 °C; typical values.
(3) T_j = 25 °C; maximum values.

Fig.3   Forward current as a function of forward
voltage.

Based on square wave currents.
T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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High-speed diodes

1N914; 1N914A; 1N914B

MGD006

Fig.5 Reverse current as a function of junction temperature.

(1) V_R = 75 V; maximum values.
(2) V_R = 75 V; typical values.
(3) V_R = 20 V; typical values.

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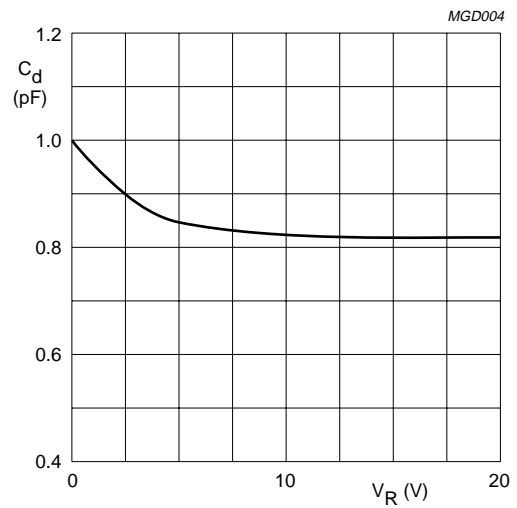
Fig.6 Diode capacitance as a function of reverse voltage; typical values.

f = 1 MHz; T_j = 25 °C.

High-speed diodes

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(1) I_R = 1 mA.

Fig.7 Reverse recovery voltage test circuit and waveforms.

Fig.8 Forward recovery voltage test circuit and waveforms.

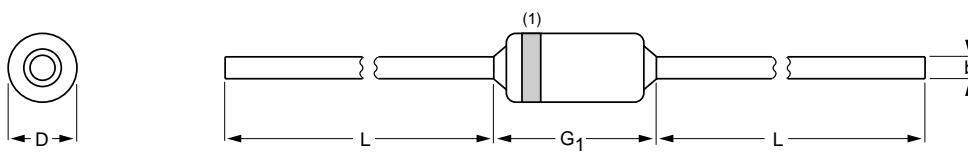Philips Semiconductors
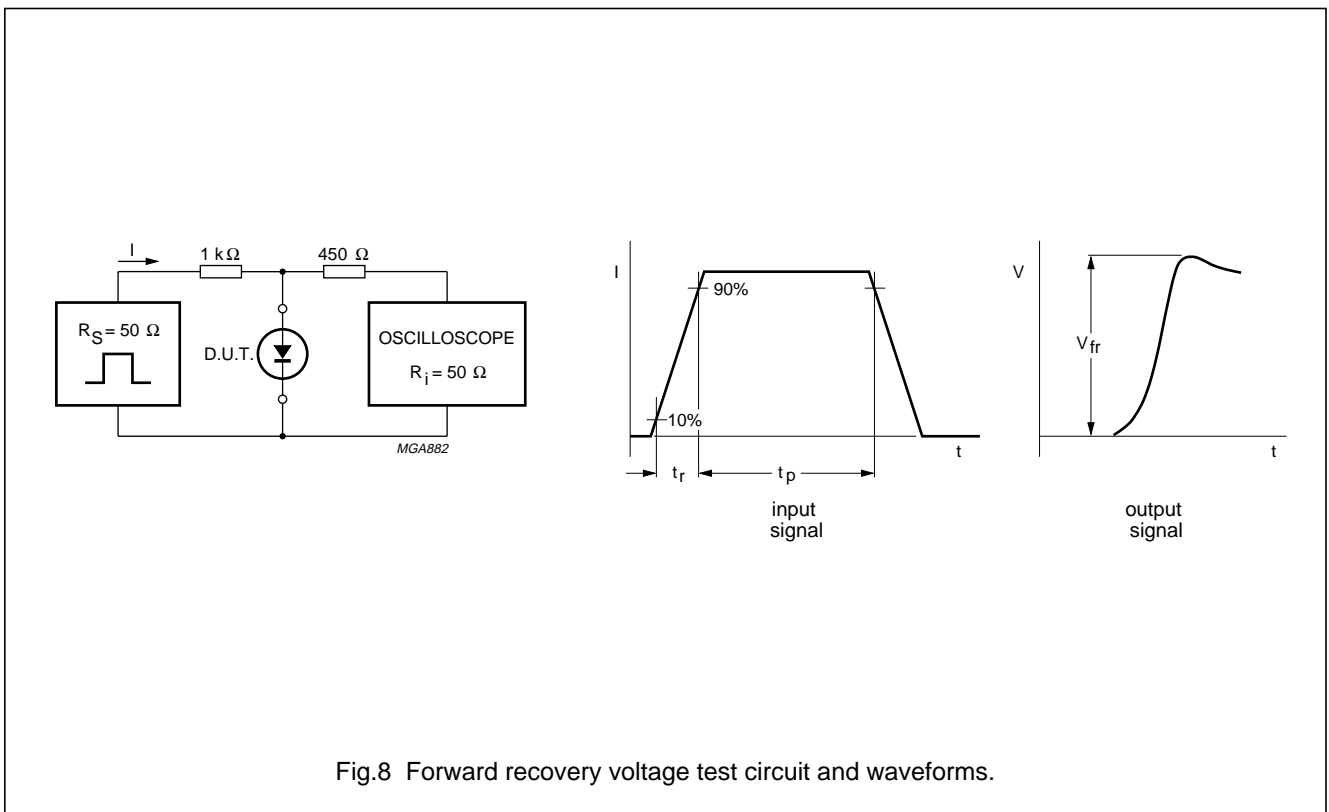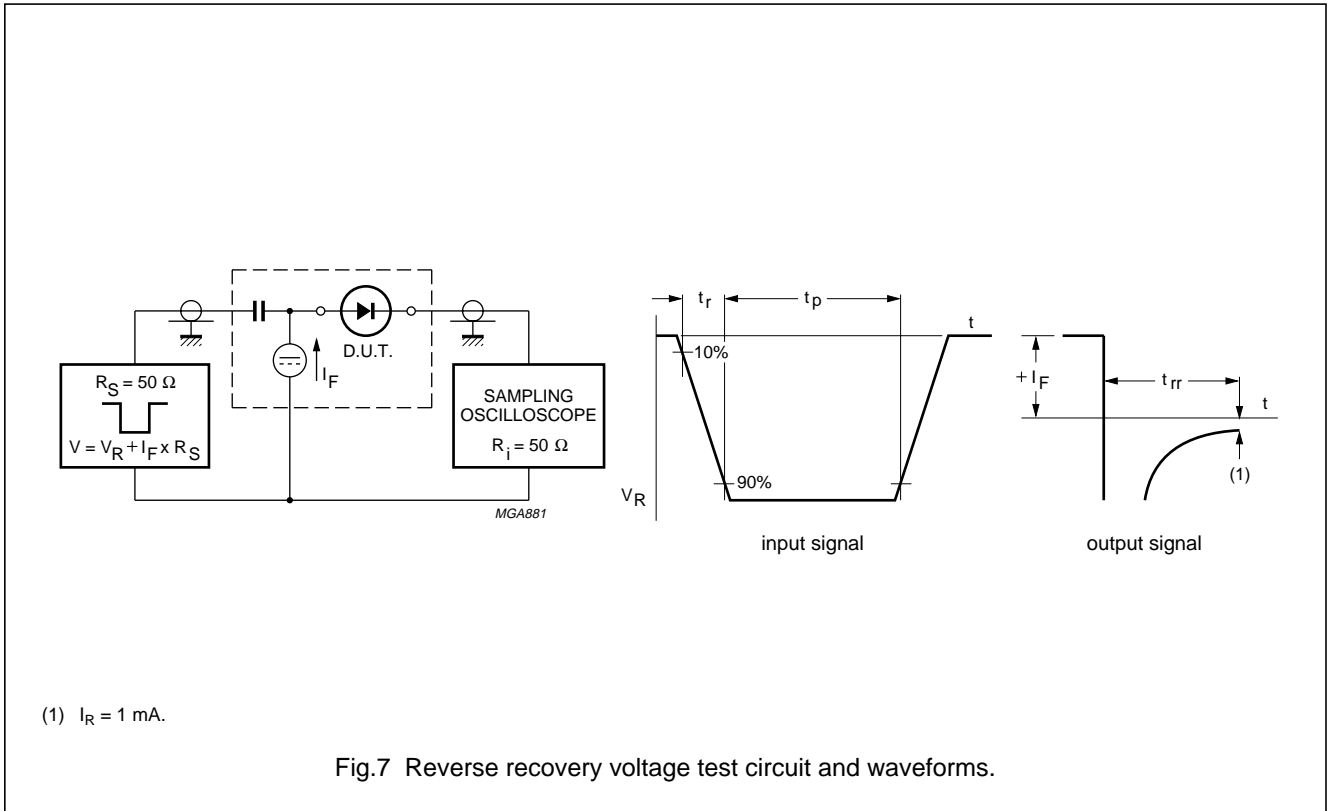
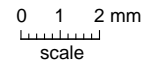|	
High-speed diodes	1N914; 1N914A; 1N914B

PACKAGE OUTLINE

Hermetically sealed glass package; axial leaded; 2 leads

SOD27

DIMENSIONS (mm are the original dimensions)

UNIT	b max.	D max.	G₁ max.	L min.
mm	0.56	1.85	4.25	25.4

Note

1. The marking band indicates the cathode.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOD27	A24	DO-35	SC-40			97-06-09

Philips Semiconductors | Product specification

High-speed diodes
1N914; 1N914A; 1N914B

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS[1]	PRODUCT STATUS[2][3]	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Notes

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2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

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Product specification

High-speed diodes

1N914; 1N914A; 1N914B

NOTES

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Product specification

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NOTES

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Product specification

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NOTES

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